

Bablu k Ghosh

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7878469/publications.pdf>

Version: 2024-02-01

51
papers

217
citations

1162367

8
h-index

1058022

14
g-index

54
all docs

54
docs citations

54
times ranked

174
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent advancements in carrier-selective contacts for high-efficiency crystalline silicon solar cells: Industrially evolving approach. <i>Nano Energy</i> , 2022, 95, 106899.	8.2	12
2	A Review on Global Emissions by E-Products Based Waste: Technical Management for Reduced Effects and Achieving Sustainable Development Goals. <i>Sustainability</i> , 2022, 14, 4036.	1.6	12
3	Numerical study of nSi and nSiGe solar cells: Emerging microstructure nSiGe cell achieved the highest 8.55% efficiency. <i>Optical Materials</i> , 2022, 129, 112539.	1.7	7
4	Morphological, structural and electrical properties of pentacene thin films grown via thermal evaporation technique. <i>Bulletin of Electrical Engineering and Informatics</i> , 2021, 10, 1291-1299.	0.6	3
5	ZnO thickness and ZnTe back contact effect of CdTe thin film solar cell Voc and efficiency progression. <i>Materials Research Express</i> , 2021, 8, 116405.	0.8	4
6	mcSi and CdTe solar photovoltaic challenges: Pathways to progress. <i>Optik</i> , 2020, 206, 164278.	1.4	9
7	High Performance Vertically Aligned Electrospun PVP:PC71BM Nanofiber for Organic Solar Cells. , 2020, , .		0
8	Enhanced Performance of Electrospun PVP:PC71BM Nanofiber for Organic Solar Cells. , 2020, , .		0
9	Low Leakage Current by Solution Processed PTAA-ZnO Transparent Hybrid Hetero-Junction Device. <i>Electronic Materials Letters</i> , 2020, 16, 457-465.	1.0	4
10	An Effective Simulation Analysis of Transient Electromagnetic Multiple Faults. <i>Sensors</i> , 2020, 20, 1976.	2.1	2
11	Dual-band polarization convertor based on electromagnetically induced transparency (EIT) effect in all-dielectric metamaterial. <i>Optics Express</i> , 2019, 27, 12163.	1.7	40
12	Emerging solar cells energy trade-off: Interface engineering materials impact on stability and efficiency progress. <i>International Journal of Energy Research</i> , 2019, 43, 1670-1688.	2.2	13
13	Recent progress in Si hetero-junction solar cell: A comprehensive review. <i>Renewable and Sustainable Energy Reviews</i> , 2018, 82, 1990-2004.	8.2	17
14	Enhancing efficiency of organic solar cells by interfacial materials modification. , 2017, , .		3
15	Frequency and voltage dependent electrical responses of poly(triarylamine) thin film-based organic Schottky diode. <i>EPJ Web of Conferences</i> , 2017, 162, 01060.	0.1	0
16	Does magnetic nano-materials in plane impedance vital for RF loss assessment?. <i>AIP Conference Proceedings</i> , 2017, , .	0.3	0
17	Enhanced Reliability of Vertical Strained Impact Ionization MOSFET Incorporating Dielectric Pocket for Ultra-Sensitive Biosensor Applications. <i>Advanced Science Letters</i> , 2017, 23, 11247-11251.	0.2	0
18	Low Voltage Wireless Power Transfer (WPT) Using Resonant Inductive Coupling Charging for Short-Range Operation. <i>Advanced Science Letters</i> , 2017, 23, 11462-11466.	0.2	0

#	ARTICLE	IF	CITATIONS
19	InGaN photocell significant efficiency enhancement on Si - an influence of interlayer physical properties. International Journal of Energy Research, 2016, 40, 1271-1279.	2.2	6
20	Novel magnetic core materials impact modelling and analysis for minimization of RF heating loss. AIP Conference Proceedings, 2016, , .	0.3	1
21	Structural properties 3,16-bis triisopropylsilylethynyl (pentacene) (TIPS-pentacene) thin films onto organic dielectric layer using slide coating method. AIP Conference Proceedings, 2015, , .	0.3	0
22	Path Planning Algorithm for Manipulators Based on an Improved Backtracking Search Algorithm. , 2015, , .		0
23	Impact of strained SiGe on the performance of Vertical Strained SiGe Impact Ionization MOSFET incorporating Dielectric Pocket (VESIMOS-DP). , 2014, , .		0
24	Performance Analysis Based on Different Indium Content for InGaN/Si Hetero-Junction Solar Cell. , 2014, , .		0
25	Characterization of vertical strained SiGe impact ionization MOSFET for ultra-sensitive biosensor application. , 2014, , .		0
26	Performance Analysis of Vertical Strained-SiGe Impact Ionization MOSFET Incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
27	Single and dual strained channel analysis of vertical strained — SiGe impact ionization MOSFET (VESIMOS). , 2013, , .		5
28	Mobility enhancement on Vertical Strained-SiGe Impact Ionization MOSFET incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
29	Performance analysis of single and dual channel vertical strained SiGe impact ionization MOSFET (VESIMOS). , 2013, , .		0
30	Mitigating Breakdown Voltage with Dual Channel Vertical Strained SiGe Impact Ionization MOSFET (VESIMOS). , 2013, , .		0
31	Impact of strain and DP position on the performance of Vertical Strained-SiGe Impact Ionization MOSFET incorporating dielectric pocket (VESIMOS-DP). , 2013, , .		1
32	Different materials coating effect on responsivity of Si UV photo detector. , 2013, , .		2
33	Body doping analysis of vertical strained-SiGe Impact Ionization MOSFET incorporating dielectric pocket (VESIMOS-DP). , 2013, , .		0
34	Optoelectronic properties of improved GaN semiconductor on Si (111) using growth approaches and different interlayer's. World Journal of Engineering, 2013, 10, 419-422.	1.0	1
35	Effects of S/D Doping Concentrations on Vertical Strained-SiGe Impact Ionization MOSFET Incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		1
36	INTENSE UV ENRICHED PHOTO DETECTION BY HIGHER ENERGY EDGE ATTUNED COATING ON CSI DETECTOR. International Journal of Research in Engineering and Technology, 2013, 02, 615-619.	0.1	1

#	ARTICLE	IF	CITATIONS
37	Optoelectronic Properties of Improved GaN Semiconductor on Si(111) Using Growth Approaches And Different Interlayer's. International Journal of Materials Science and Applications, 2013, 2, 43.	0.1	0
38	Compatibility issues of Si technology with higher band gap materials for RF applications. , 2012, , .		0
39	Photo detector junction properties and dynamic aptness analysis — Computational study. , 2012, , .		0
40	Investigation of incorporating dielectric pocket (DP) on Vertical Strained-SiGe Impact Ionization MOSFET (VESIMOS-DP). , 2012, , .		7
41	Enhanced performance analysis of vertical strained-sigeimpact Ionization MOSFET (VESIMOS). , 2012, , .		9
42	High luminescence efficient Ga polarity domain GaN realized on Si(111) by MOVPE. , 2011, , .		0
43	Organometallic vapor phase epitaxial growth of GaN on a 3c-SiC/Si(111) template formed by C+ion implantation into Si(111) substrate. Journal of Crystal Growth, 2004, 261, 266-270.	0.7	17
44	Formation of air-gap structure at a GaN epilayer/substrate interface by using an InN interlayer. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2826-2829.	0.8	3
45	A comparative study on In-doping effects for MOVPE GaN films on Si(111) and sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2562-2565.	0.8	1
46	Improvement of the optical properties of GaN epilayers on Si(111): Impact of GaAs layer thickness on Si and pre-growth strategy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2725-2728.	0.8	0
47	Reduced-stress GaN epitaxial layers grown on Si(111) by using a porous GaN interlayer converted from GaAs. Journal of Crystal Growth, 2003, 249, 422-428.	0.7	35
48	Conductance and Capacitance Responses of Metal-Organic-Metal Structure Based Organic Semiconductor Thin Film. Solid State Phenomena, 0, 268, 264-268.	0.3	0
49	Design and Simulation Analysis of Vertical Double-Gate MOSFET (VDGM) Structure for Nano-Device Application. International Journal of Simulation: Systems, Science and Technology, 0, , .	0.0	0
50	Doping Concentrations Analysis on The Performance of Vertical Strained-SiGe Impact Ionization MOSFET Incorporating Dielectric Pocket (VESIMOS-DP). International Journal of Simulation: Systems, Science and Technology, 0, , .	0.0	0
51	Breakdown Voltage Reduction Analysis with Adopting Dual Channel Vertical Strained SiGe Impact Ionization MOSFET (VESIMOS). International Journal of Simulation: Systems, Science and Technology, 0, , .	0.0	1